

4V Drive Pch MOSFET

RSJ250P10

● Structure

Silicon P-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.

● Application

Switching

● Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	1000
RSJ250P10		○

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V_{DSS}	-100	V	
Gate-source voltage	V_{GSS}	±20	V	
Drain current	Continuous	I_D *1	±25	A
	Pulsed	I_{DP} *2	±50	A
Source current (Body Diode)	Continuous	I_S *1	-25	A
	Pulsed	I_{SP} *2	-50	A
Power dissipation	P_D *3	50	W	
Channel temperature	Tch	150	°C	
Range of storage temperature	Tstg	-55 to +150	°C	

*1 Limited only by maximum temperature allowed.

*2 $P_W \leq 10\mu s$, Duty cycle $\leq 1\%$

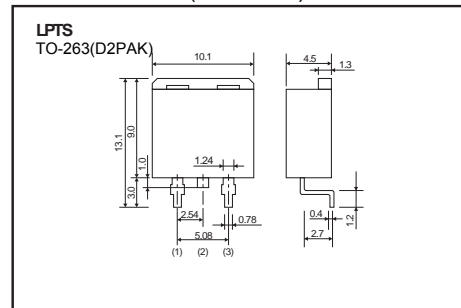
*3 $T_C = 25^\circ C$

● Thermal resistance

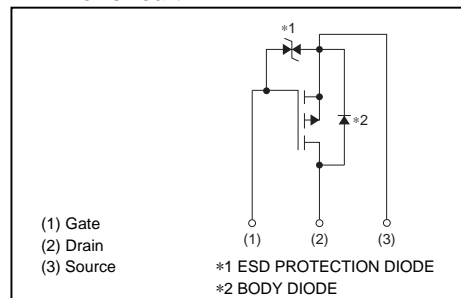
Parameter	Symbol	Limits	Unit
Channel to Ambient	$R_{th}(ch-c)^*$	2.5	°C / W

* $T_C = 25^\circ C$

● Dimensions (Unit : mm)



● Inner circuit



● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-100	-	-	V	$I_D=-1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	-	-	-1	μA	$V_{DS}=-100V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	-1.0	-	-2.5	V	$V_{DS}=-10V, I_D=-1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	45	63	m Ω	$I_D=-25A, V_{GS}=-10V$
		-	48	67		$I_D=-12.5A, V_{GS}=-4.5V$
		-	50	70		$I_D=-12.5A, V_{GS}=-4.0V$
Forward transfer admittance	$ Y_{fs} ^*$	20	-	-	S	$I_D=-25A, V_{DS}=-10V$
Input capacitance	C_{iss}	-	8000	-	pF	$V_{DS}=-25V$
Output capacitance	C_{oss}	-	300	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	-	200	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	30	-	ns	$I_D=-12.5A, V_{DD} \approx -50V$
Rise time	t_r^*	-	67	-	ns	$V_{GS}=-10V$
Turn-off delay time	$t_{d(off)}^*$	-	310	-	ns	$R_L=4\Omega$
Fall time	t_f^*	-	180	-	ns	$R_G=10\Omega$
Total gate charge	Q_g^*	-	60	-	nC	$I_D=-25A$
Gate-source charge	Q_{gs}^*	-	17	-	nC	$V_{DD} \approx -50V$
Gate-drain charge	Q_{gd}^*	-	19	-	nC	$V_{GS}=-5V$

*Pulsed

● Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	-1.2	V	$I_S=-25A, V_{GS}=0V$

*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics (I)

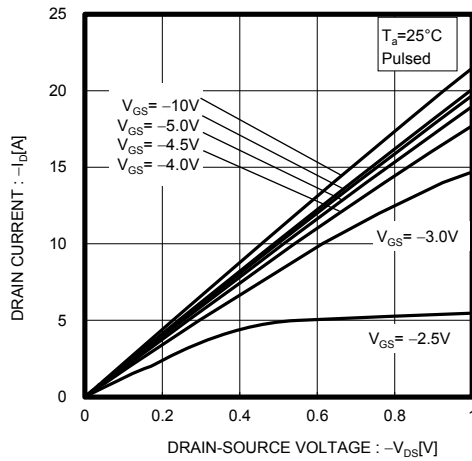


Fig.2 Typical Output Characteristics (II)

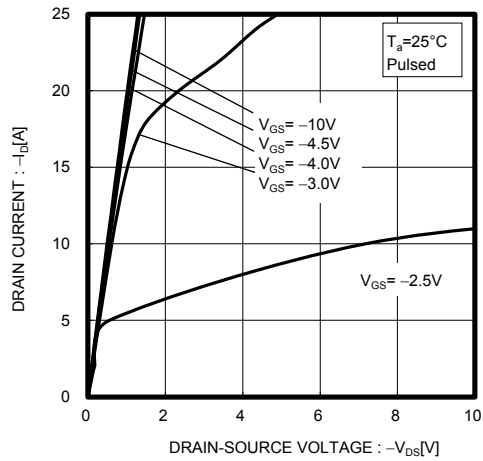


Fig.3 Typical Transfer Characteristics

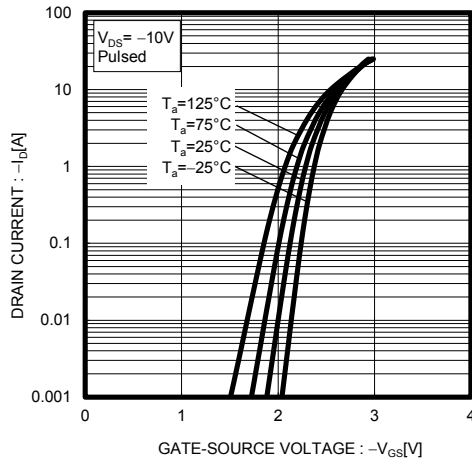


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (I)

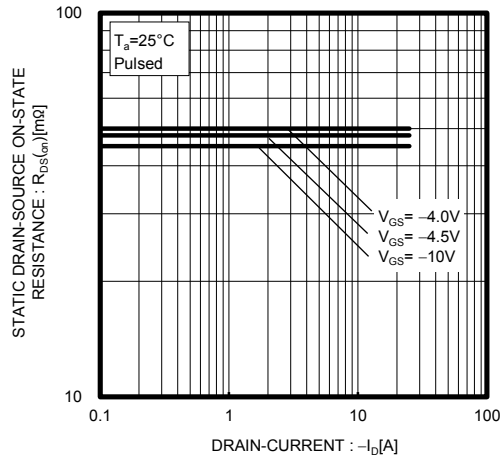


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (II)

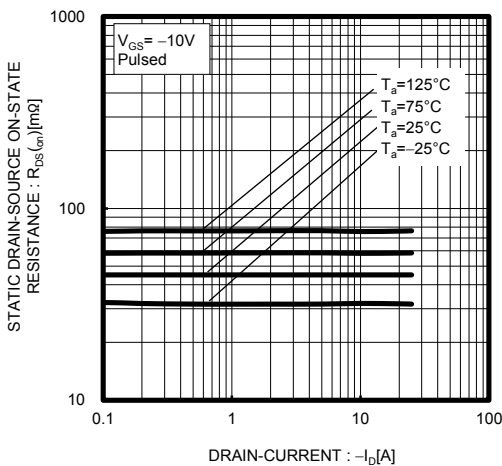


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current (III)

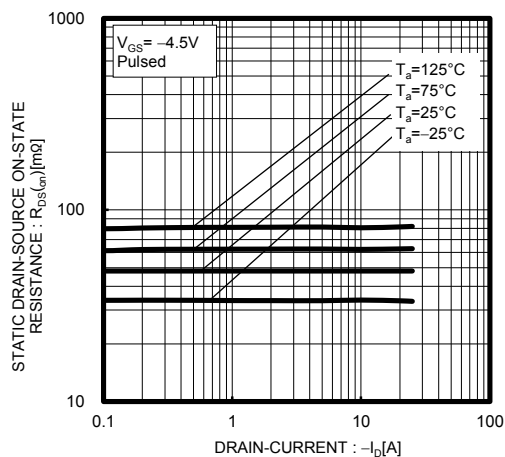


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (IV)

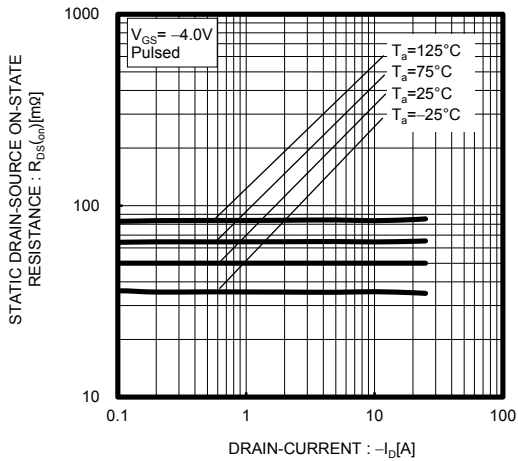


Fig.8 Forward Transfer Admittance vs. Drain Current

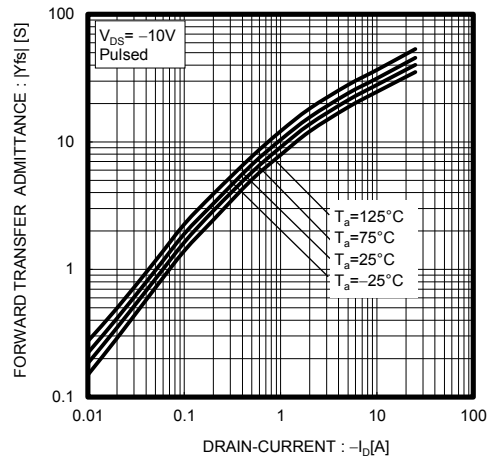


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

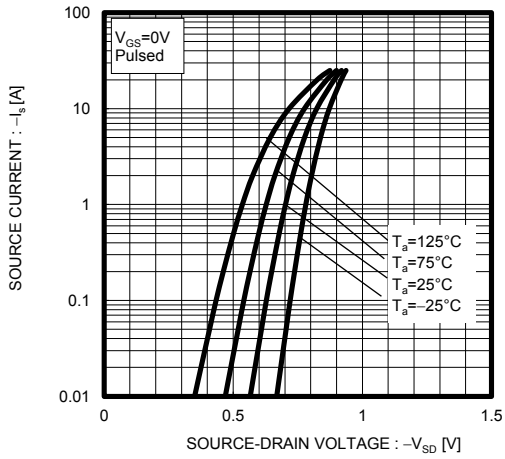


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

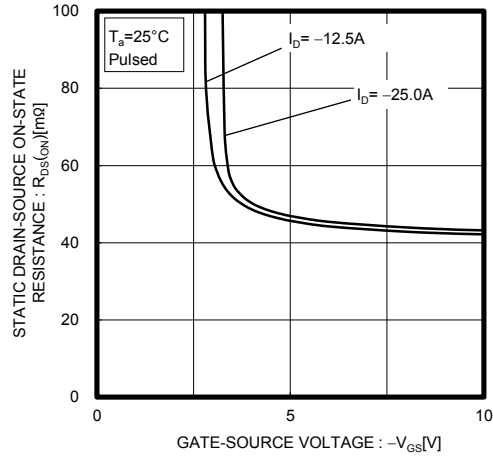


Fig.11 Switching Characteristics

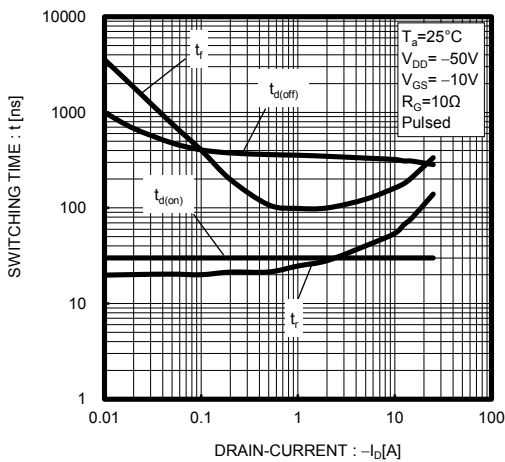


Fig.12 Dynamic Input Characteristics

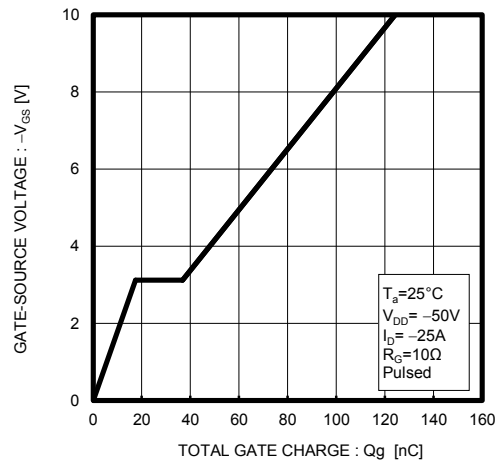


Fig.13 Typical Capacitance vs. Drain-Source Voltage

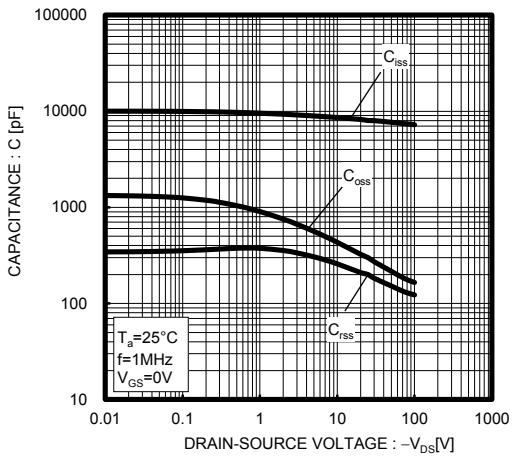


Fig.14 Maximum Safe Operating Area

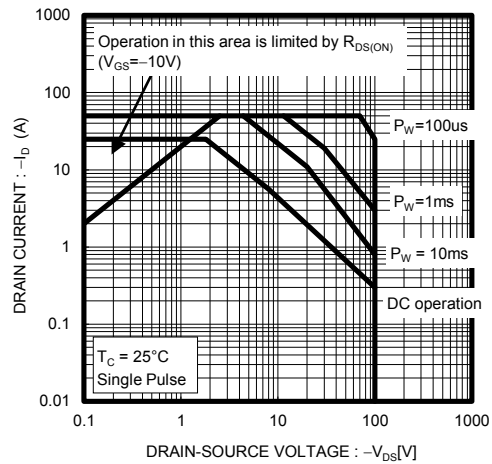
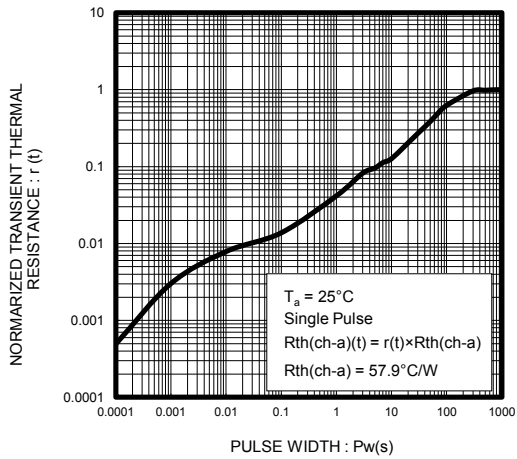


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width



● Measurement circuits

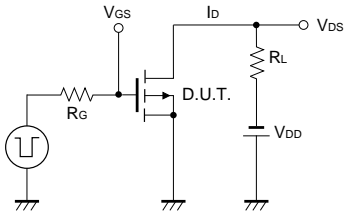


Fig.1-1 Switching Time Measurement Circuit

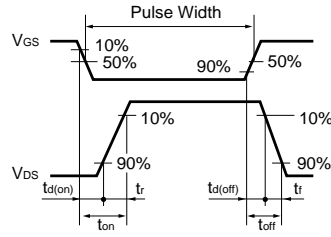


Fig.1-2 Switching Waveforms

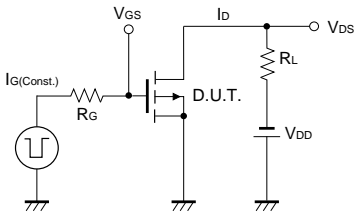


Fig.2-1 Gate Charge Measurement Circuit

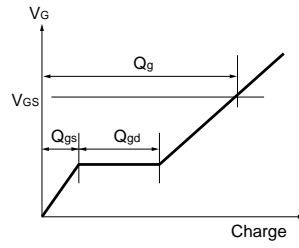


Fig.2-2 Gate Charge Waveform

Notes

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